providing a first layer above a gate dielectric layer, the gate dielectric layer being above a substrate, the first layer including silicon oxynitride or silicon rich nitride;

providing a second layer above the first layer;

forming a first aperture in the second layer;

forming a second aperture in the first layer utilizing a RELACS process the second aperture being narrower than the first aperture;

filling the first aperture and the second aperture with a gate conductor material; and

removing the gate conductor material above the second layer.

16. (Amended) The method of claim 15, wherein

the second layer is an oxide layer [above the first layer and forming an aperture in the oxide layer before forming the aperture in the first layer].

19. (Amended) The method ~~of~~ claim 16, wherein the gate conductor material is silicided.